

205-187

UMC



UM6264 Series

8K×8 CMOS SRAM

um6264-121

Features

- Single +5 volt power supply
- Access times: 70/100/120 ns (max.)
- Current:
 - Standard version: Operating: 90 mA (max.)
 - Standby: 2 mA (max.)
 - Low power version: Operating: 90 mA (max.)
 - Standby: 100 μ A (max.)
- Fully static operation, no clock or refreshing required
- Directly TTL compatible. All inputs and outputs
- Common I/O using three-state output

- Output enable and two chip select inputs for easy application
- Data retention voltage: 2V (min) for low power version
- UM6264-70/10/12 is the standard version
- UM6264-70L/10L/12L is the low power version
- UM6264-70T/10T/12T is the wide temperature version
- UM6264-70LT/10LT/12LT is the low power, wide temperature version
- Available in 28 pin DIP, SOP, or Skinny DIP packages (See ordering information page 9)

General Description

The UM6264 is a high-speed, low-power 65,536-bit static random access memory organized as 8,192 words by 8 bits and operates on a single 5-volt power supply. It is built using UMC's high performance CMOS process.

Inputs and three-state outputs are TTL compatible and allow for direct interfacing with common system bus structures.

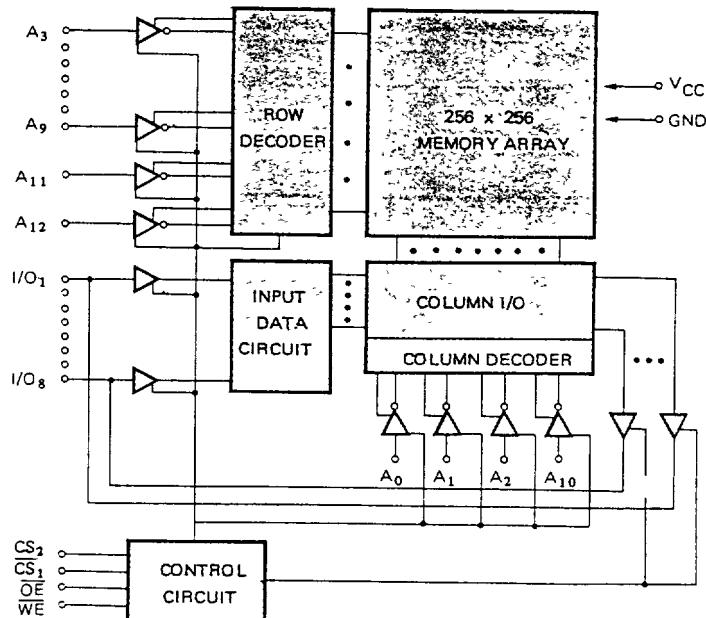
Two chip select inputs are provided for power down and device select, and an output enable input is included for easy interface.

Data retention is guaranteed at a power supply voltage as low as 2V for the low power version.

Pin Configuration

NC	1	28	V _{CC}
A ₁₂	2	27	WE
A ₇	3	26	CS ₂
A ₆	4	25	A ₈
A ₅	5	24	A ₉
A ₄	6	23	A ₁₁
A ₃	7	22	OE
A ₂	8	21	A ₁₀
A ₁	9	20	CS ₁
A ₀	10	19	I/O ₈
I/O ₁	11	18	I/O ₇
I/O ₂	12	17	I/O ₆
I/O ₃	13	16	I/O ₅
GND	14	15	I/O ₄

Block Diagram





UM6264 Series

Pin Description

Designation	Description
$A_0 \sim A_{12}$	Address Input
WE	Write Enable
OE	Output Enable
\overline{CS}_1	Chip Select
CS_2	Chip Select
NC	No Connection
$I/O_1 \sim I/O_8$	Data Input/Output
V_{CC}	Power Supply (+5V)
GND	Ground

Recommended DC Operating Conditions

($T_A = 0^\circ C$ to $70^\circ C$ for UM6264-70/10/12, UM6264-70L/10L/12L, $T_A = -40^\circ C$ to $85^\circ C$ for UM6264-70T/10T/12T, UM6264-70LT/10LT/12LT)

Symbol	Parameter	Min.	Typ.	Max.	Unit
V_{CC}	Supply Voltage	4.5	5.0	5.5	V
GND	Ground	0	0	0	V
V_{IH}	Input High Voltage	2.2	3.5	$V_{CC} + 0.5V$	V
V_{IL}	Input Low Voltage	-0.3	0	+0.8	V
C_L	Output Load	—	—	100	pF
TTL	Output Load	—	—	1	—

Absolute Maximum Ratings *

V_{CC} to GND $-0.5V$ to $+7.0V$
 IN, IN/OUT Volt to GND $-0.5V$ to $V_{CC} + 0.5V$
 Operating Temperature, T_{opr} . . . $0^\circ C$ to $+70^\circ C$ (Note 1)
 Storage Temperature, T_{stg} . . . $-55^\circ C$ to $+125^\circ C$
 Temperature Under Bias, T_{bias} . . . $-10^\circ C$ to $+85^\circ C$ (Note 1)
 Power Dissipation, P_T 1.0W/SOP 0.7W
 Soldering temp. & time $260^\circ C$, 10 sec
 Note 1. for UM6264-70T/10T/12T, UM6264-70LT/10LT/12LT. ($T_{opr} = -40^\circ C$ to $85^\circ C$; $T_{bias} = -50^\circ C$ to $95^\circ C$)

DC Electrical Characteristics

($T_A = 0^\circ C$ to $+70^\circ C$, $V_{CC} = 5V \pm 10\%$, GND = 0V, $T_A = -40^\circ C$ to $85^\circ C$ for T and LT versions)

Symbol	Parameter	UM6264-70/10/12/70T/10T/12T		UM6264-70L/10L/12L/70LT/10LT/12LT		Unit	Conditions
		Min.	Max.	Min.	Max.		
I_{IL}	Input Leakage Current	—	2	—	2	μA	$V_{IN} = GND$ to V_{CC}
I_{LO}	Output Leakage Current	—	2	—	2	μA	$\overline{CS}_1 = V_{IH}$ or $CS_2 = V_{IL}$ or $OE = V_{IH}$ or $WE = V_{IL}$ $V_{I/O} = GND$ to V_{CC}
I_{CC}	Active Power Supply Current	—	90	—	90	mA	$\overline{CS}_1 = V_{IL}$, $CS_2 = V_{IH}$ $I_{I/O} = 0 mA$
I_{CC1}	Dynamic Operating Current	—	90	—	90	mA	Min. Cycle, Duty = 100% $\overline{CS}_1 = V_{IL}$, $CS_2 = V_{IH}$ $I_{I/O} = 0 mA$
I_{SB}	Standby Power Supply Current	—	5	—	3	mA	$\overline{CS}_1 = V_{IH}$ or $CS_2 = V_{IL}$
I_{SB1}		—	2	—	0.1	mA	$CS_1 \geq V_{CC} - 0.2V$, $CS_2 \geq V_{CC} - 0.2V$, $V_{IN} \geq V_{CC} - 0.2V$ or $V_{IN} \leq 0.2V$
I_{SB2}		—	2	—	0.1	mA	$CS_1 \leq 0.2V$, $CS_2 \leq 0.2V$ $V_{IN} \geq V_{CC} - 0.2V$, or $V_{IN} \leq 0.2V$
V_{OL}	Output Low Voltage	—	0.4	—	0.4	V	$I_{OL} = 4 mA$
V_{OH}	Output High Voltage	2.4	—	2.4	—	V	$I_{OH} = -1.0 mA$

Truth Table

Mode	\overline{CS}_1	CS_2	\overline{OE}	\overline{WE}	I/O Operation	V_{CC} Current
Standby	H	X	X	X	High Z	I_{SB}, I_{SB1}
	X	L	X	X	High Z	I_{SB}, I_{SB2}
Output Disabled	L	H	H	H	High Z	I_{CC}, I_{CC1}
Read	L	H	L	H	D_{OUT}	I_{CC}, I_{CC1}
Write	L	H	X	L	D_{IN}	I_{CC}, I_{CC1}

Note X = H or L

Capacitance ($T_A = 25^\circ C, f = 10 \text{ MHz}$)

Symbol	Parameter	Min.	Max.	Unit	Conditions
C_{IN}^*	Input Capacitance		6	pF	$V_{IN} = 0V$
$C_{I/O}^*$	Input/Output Capacitance		8	pF	$V_{I/O} = 0V$

* This parameter is sampled and not 100% tested

AC Characteristics ($V_{CC} = 5V \pm 10\%, T_A = 0^\circ \text{ to } +70^\circ C$ for UM6264-70/10/12, UM6264-70L/10L/12L
 $T_A = -40^\circ C \text{ to } 85^\circ C$ for UM6264-70T/10T/12T, UM6264-70LT/10LT/12LT)

Symbol	Parameter	UM6264-70/70L 70T/70LT Min.	UM6264-10/10L 10T/10LT Min.	UM6264-12/12L 12T/12LT Min.	Unit
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Read Cycle

t_{RC}	Read Cycle Time	70	—	100	—	120	—	ns
t_{AA}	Address Access Time	—	70	—	100	—	120	ns
t_{ACS1}	Chip Select Access Time	\overline{CS}_1	—	70	—	100	—	120
	Time		CS_2	—	70	—	100	—
t_{OE}	Output Enable to Output Valid	—	35	—	50	—	60	ns
t_{CLZ1}	Chip Selection to Output in Low Z	\overline{CS}_1	10	—	10	—	10	—
	CS_2		10	—	10	—	10	—
t_{OLZ}	Output Enable to Output in Low Z	5	—	5	—	5	—	ns
t_{CHZ1}	Chip Deselection to Output in High Z	\overline{CS}_1	0	35	0	35	0	40
	CS_2		0	35	0	35	0	40
t_{OHZ}	Output Disable to Output in High Z	0	30	0	35	0	40	ns
t_{OH}	Output Hold from Address Change	10	—	10	—	10	—	ns

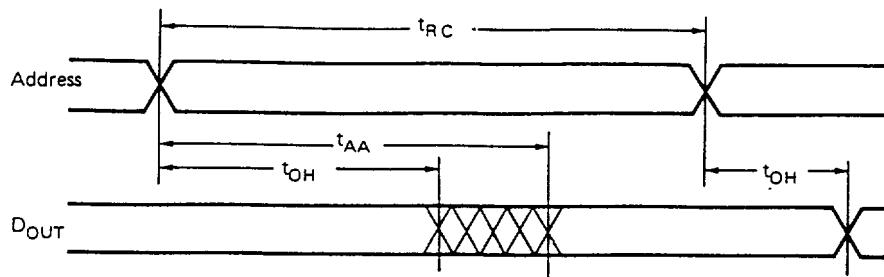
Write Cycle

t_{WC}	Write Cycle Time	70	—	100	—	120	—	ns
t_{CW}	Chip Selection to End of Write	60	—	80	—	85	—	ns
t_{AS}	Address Set-up Time	0	—	0	—	0	—	ns
t_{AW}	Address Valid to End of Write	60	—	80	—	85	—	ns
t_{WP}	Write Pulse Width	50	—	60	—	70	—	ns
t_{WR}	Write Recovery Time	0	—	0	—	0	—	ns
t_{WHZ}	Write to Output in High Z	0	30	0	35	0	40	ns
t_{DW}	Data to Write Time Overlap	30	—	40	—	50	—	ns
t_{DH}	Data Hold from Write Time	0	—	0	—	0	—	ns
t_{OHZ}	Output Disable to Output in High Z	0	30	0	35	0	40	ns
t_{OW}	Output Active from End of Write	5	—	10	—	10	—	ns

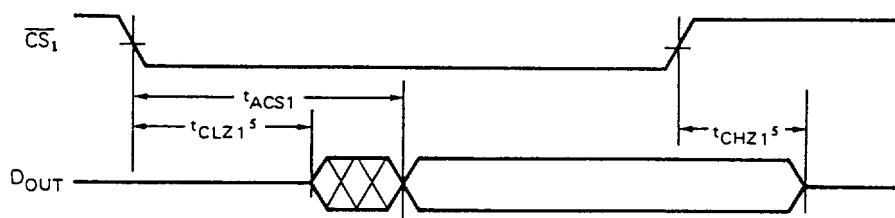
Notes t_{CHZ} , t_{OHZ} and t_{WHZ} are defined as the time at which the outputs achieve the open circuit condition and are not referred to output voltage levels

Timing Waveforms (Continued)

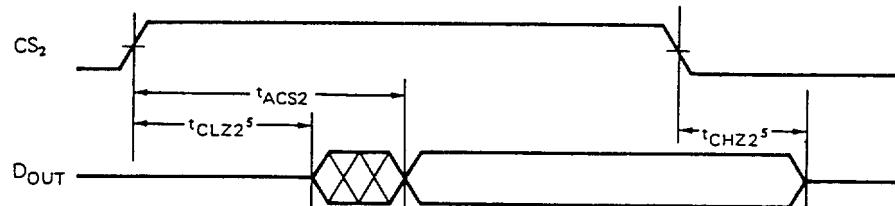
Read Cycle 1^(1,2,4)



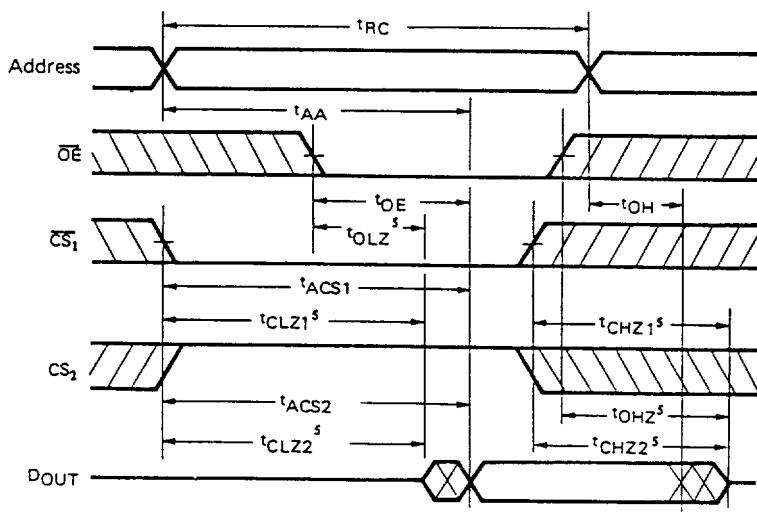
Read Cycle 2^(1,3,4,6)



Read Cycle 3^(1,4,7,8)



Read Cycle 4⁽¹⁾



Notes. 1. \overline{WE} is high for READ cycle.

2. Device is continuously selected $\overline{CS}_1 = V_{IL}$ and $CS_2 = V_{IH}$.

3. Address valid prior to or coincident with \overline{CS}_1 transition low.

4. $\overline{OE} = V_{IL}$.

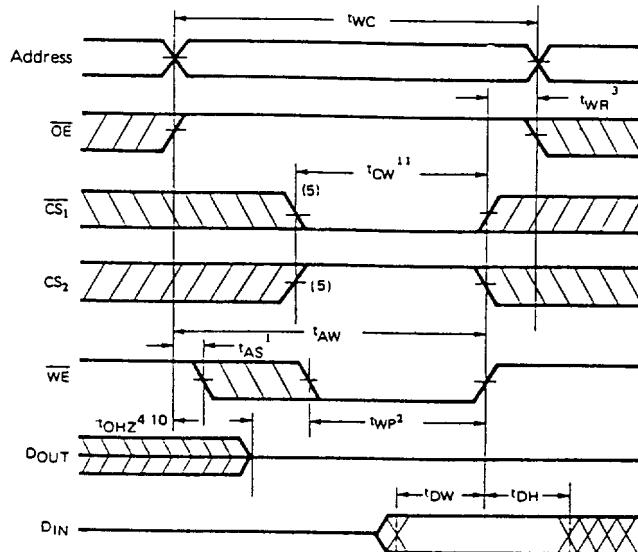
5. Transition is measured $\pm 500\text{mV}$ from steady state. This parameter is sampled and not 100% tested.
6. CS_2 is high.

7. \overline{CS}_1 is low.

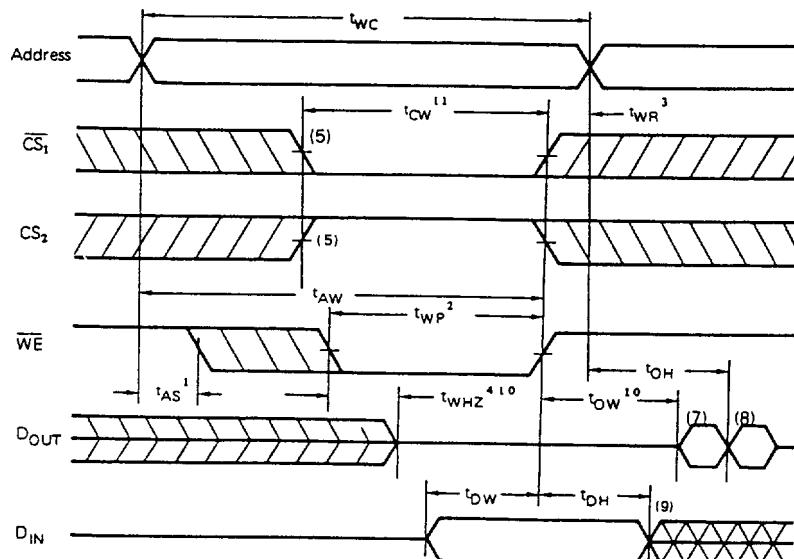
8. Address valid prior to or coincident with CS_2 transition high

Timing Waveforms (Continued)

Write Cycle 1



Write Cycle 2⁽⁶⁾



- Notes
1. t_{AS} is measured from the address valid to the beginning of write
 2. A write occurs during the overlap (t_{WP}) of a low \overline{CS}_1 , a high \overline{CS}_2 and a low \overline{WE} .
 3. t_{WR} is measured from the earliest of \overline{CS}_1 or \overline{WE} going high or \overline{CS}_2 going low to the end of write cycle.
 4. During this period, I/O pins are in the output state so that the input signals of opposite phase to the outputs must not be applied.
 5. If the \overline{CS}_1 low transition or the \overline{CS}_2 high transition occur simultaneously with the \overline{WE} low transition or after the \overline{WE} transition, outputs remain in a high impedance state.
 6. \overline{OE} is continuously low ($\overline{OE} = V_{IL}$)
 7. D_{OUT} is the same phase of write data of this write cycle.
 8. D_{OUT} is the read data of next address.
 9. If \overline{CS}_1 is low and \overline{CS}_2 is high during this period, I/O pins are in the output state. The data input signals of opposite phase to the outputs must not be applied to I/O pins
 10. Transition is measured $\pm 500\text{mV}$ from steady state. This parameter is sampled and not 100% tested
 11. t_{CW} is measured from the later of \overline{CS}_1 going low or \overline{CS}_2 going high to the end of write.

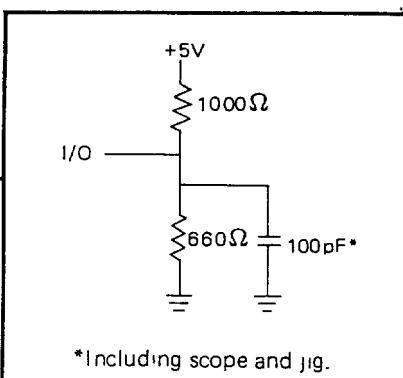
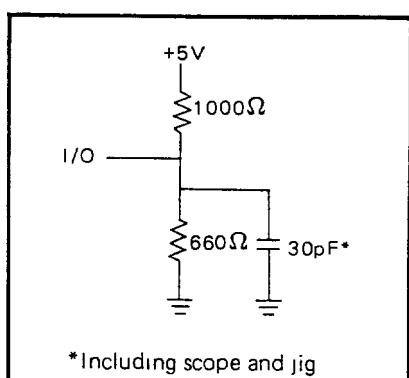
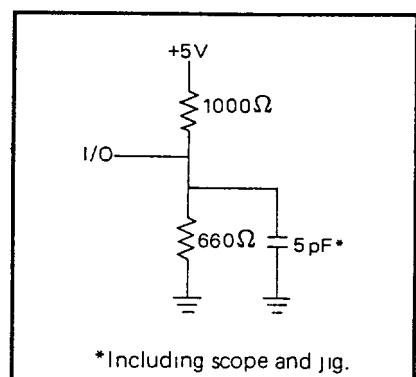
AC Test Conditions

For Access Time 70ns

Input Pulse Levels	0V to 3.0V
Input Rise and Fall Times	5ns
Input and Output Timing Reference Levels	1.5V
Output Load	See Fig. 2, 3

For Access Times. 100/120 ns

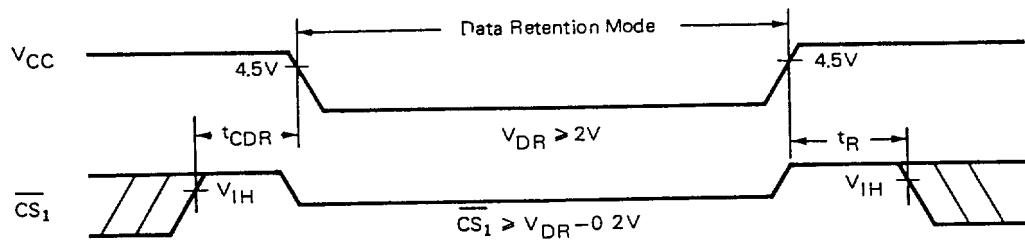
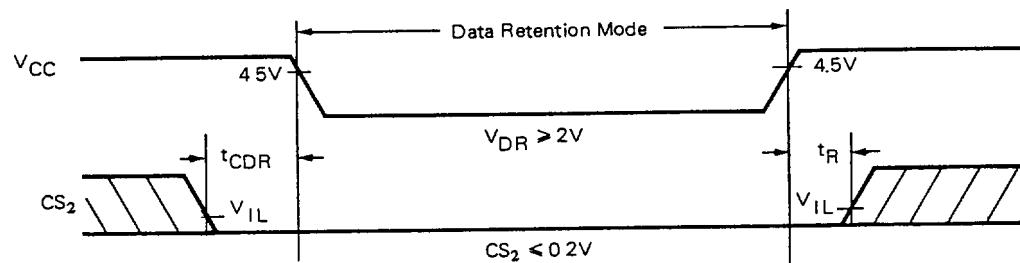
Input Pulse Levels	0.8V to 2.2V
Input Rise and Fall Times	5ns
Input and Output Timing Reference Levels	1.5V
Output Load	See Fig. 1, 3

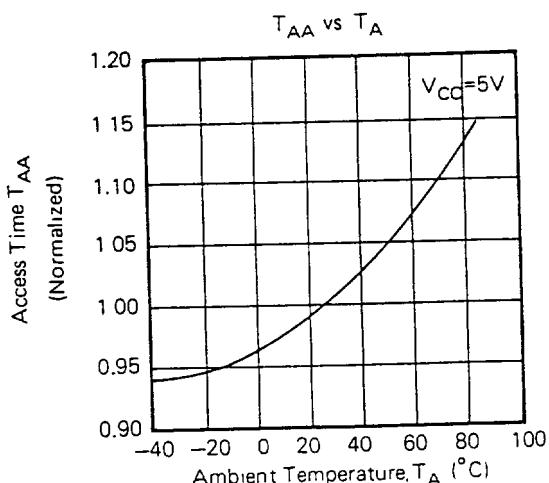
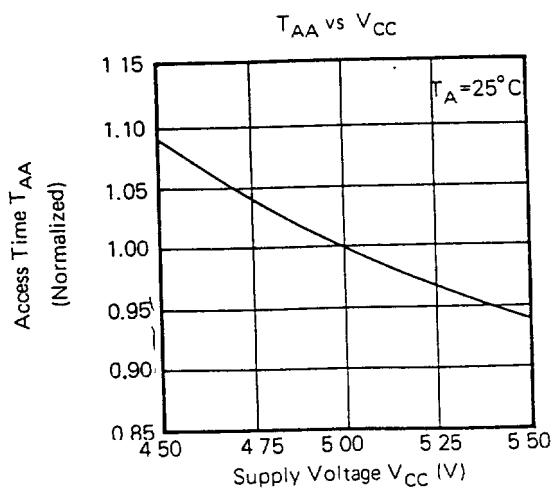
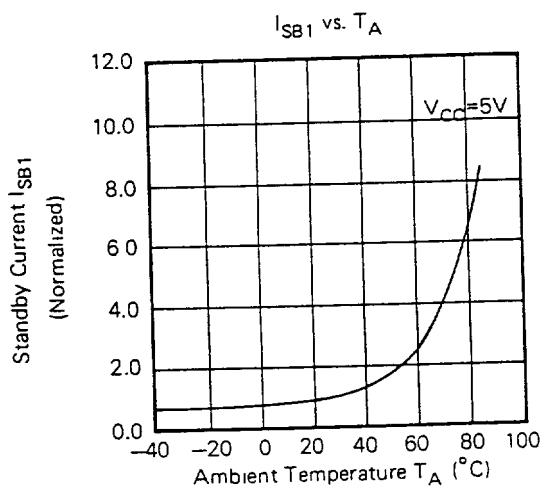
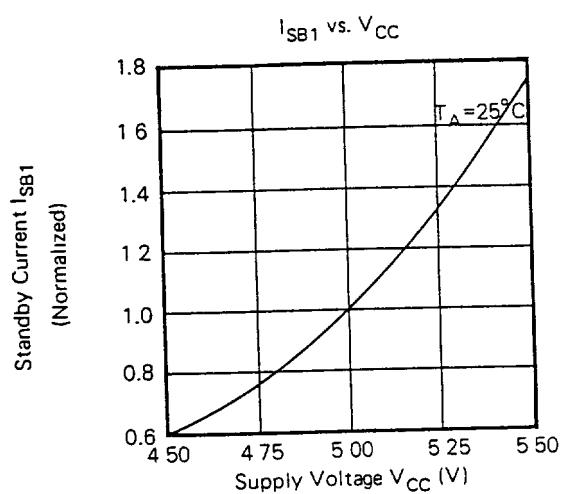
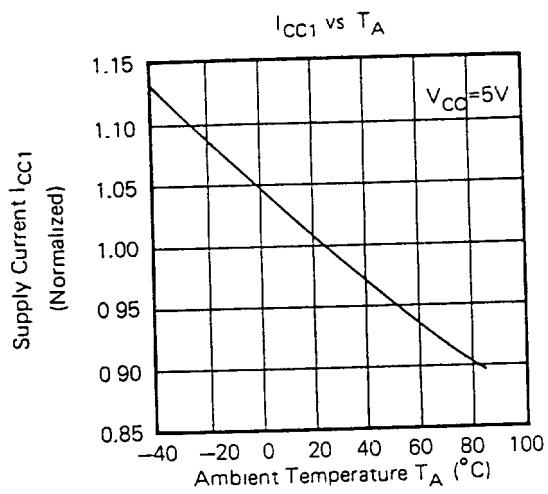
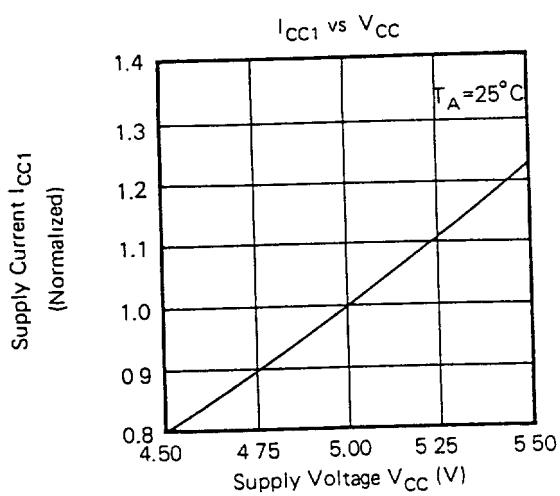

Figure 1. Output Load

Figure 2. Output Load

Figure 3. Output Load for t_{CLZ} , t_{OLZ} , t_{CHZ} , t_{OHZ} , t_{WHZ} , and t_{OW}

Data Retention Characteristics (L version only, $T_A = 0^\circ\text{C}$ to 70°C for UM6264-70L/10L/12L; $T_A = -40^\circ\text{C}$ to 85°C for UM6264-70LT/10LT/12LT)

Symbol	Parameter	Min.	Max.	Unit	Conditions
V_{DR1}	V_{CC} for Data Retention	2.0	5.5	V	$\overline{CS}_1 \geq V_{CC} - 0.2V$, $CS_2 \geq V_{CC} - 0.2V$ or $CS_2 \leq 0.2V$
V_{DR2}		2.0	5.5	V	$CS_2 \leq 0.2V$
I_{CCDR1}	Data Retention Current	—	50	μA	$V_{CC} = 3.0V$, $\overline{CS}_1 \geq V_{CC} - 0.2V$, $CS_2 \geq V_{CC} - 0.2V$, $V_{IN} \geq V_{CC} - 0.2V$ or $V_{IN} \leq 0.2V$
I_{CCDR2}		—	50	μA	$V_{CC} = 3.0V$, $CS_2 \leq 0.2V$, $\overline{CS}_1 \leq 0.2V$, $V_{IN} \geq V_{CC} - 0.2V$ or $V_{IN} \leq 0.2V$
t_{CDR}	Chip Deselect to Data Retention Time	0	—	ns	See Retention Waveform
t_R	Operation Recovery Time	t_{RC}^*	—	ns	

* t_{RC} = Read Cycle Time

Low V_{CC} Data Retention Waveform (1) (\overline{CS}_1 Controlled)

Low V_{CC} Data Retention Waveform (2) (CS_2 Controlled)


Characteristic Curves




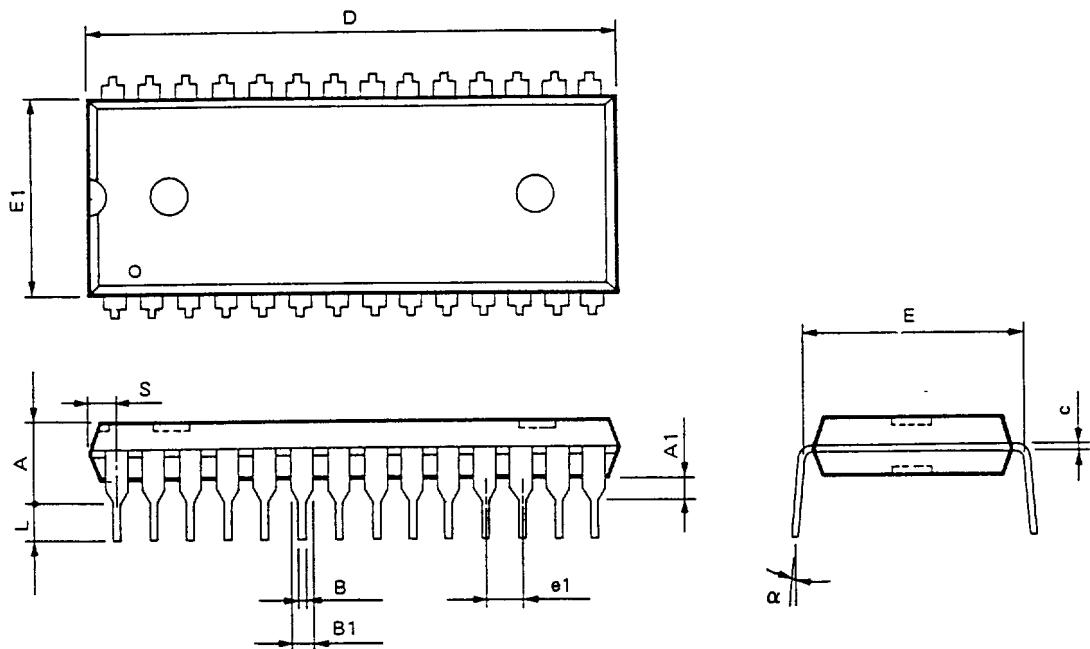
Ordering Information

Part No.	Access Time (ns)	Operating Current Max. (mA)	Standby Current Max. (mA)	Temperature Range	Package
UM6264-70	70	90	2	0°C to 70°C	28L DIP
UM6264-70L		90	0.1	0°C to 70°C	28L DIP
UM6264-70T		90	2	-40°C to 85°C	28L DIP
UM6264-70LT		90	0.1	-40°C to 85°C	28L DIP
UM6264M-70		90	2	0°C to 70°C	28L SOP
UM6264M-70L		90	0.1	0°C to 70°C	28L SOP
UM6264M-70T		90	2	-40°C to 85°C	28L SOP
UM6264M-70LT		90	0.1	-40°C to 85°C	28L SOP
UM6264K-70		90	2	0°C to 70°C	28L Skinny
UM6264K-70L		90	0.1	0°C to 70°C	28L Skinny
UM6264K-70T		90	2	-40°C to 85°C	28L Skinny
UM6264K-70LT		90	0.1	-40°C to 85°C	28L Skinny
UM6264-10	100	90	2	0°C to 70°C	28L DIP
UM6264-10L		90	0.1	0°C to 70°C	28L DIP
UM6264-10T		90	2	-40°C to 85°C	28L DIP
UM6264-10LT		90	0.1	-40°C to 85°C	28L DIP
UM6264M-10		90	2	0°C to 70°C	28L SOP
UM6264M-10L		90	0.1	0°C to 70°C	28L SOP
UM6264M-10T		90	2	-40°C to 85°C	28L SOP
UM6264M-10LT		90	0.1	-40°C to 85°C	28L SOP
UM6264K-10		90	2	0°C to 70°C	28L Skinny
UM6264K-10L		90	0.1	0°C to 70°C	28L Skinny
UM6264K-10T		90	2	-40°C to 85°C	28L Skinny
UM6264K-10LT		90	0.1	-40°C to 85°C	28L Skinny
UM6264-12	120	90	2	0°C to 70°C	28L DIP
UM6264-12L		90	0.1	0°C to 70°C	28L DIP
UM6264-12T		90	2	-40°C to 85°C	28L DIP
UM6264-12LT		90	0.1	-40°C to 85°C	28L DIP
UM6264M-12		90	2	0°C to 70°C	28L SOP
UM6264M-12L		90	0.1	0°C to 70°C	28L SOP
UM6264M-12T		90	2	-40°C to 85°C	28L SOP
UM6264M-12LT		90	0.1	-40°C to 85°C	28L SOP
UM6264K-12		90	2	0°C to 70°C	28L Skinny
UM6264K-12L		90	0.1	0°C to 70°C	28L Skinny
UM6264K-12T		90	2	-40°C to 85°C	28L Skinny
UM6264K-12LT		90	0.1	-40°C to 85°C	28L Skinny

Package Information

28 LEAD DUAL IN-LINE; PLASTIC

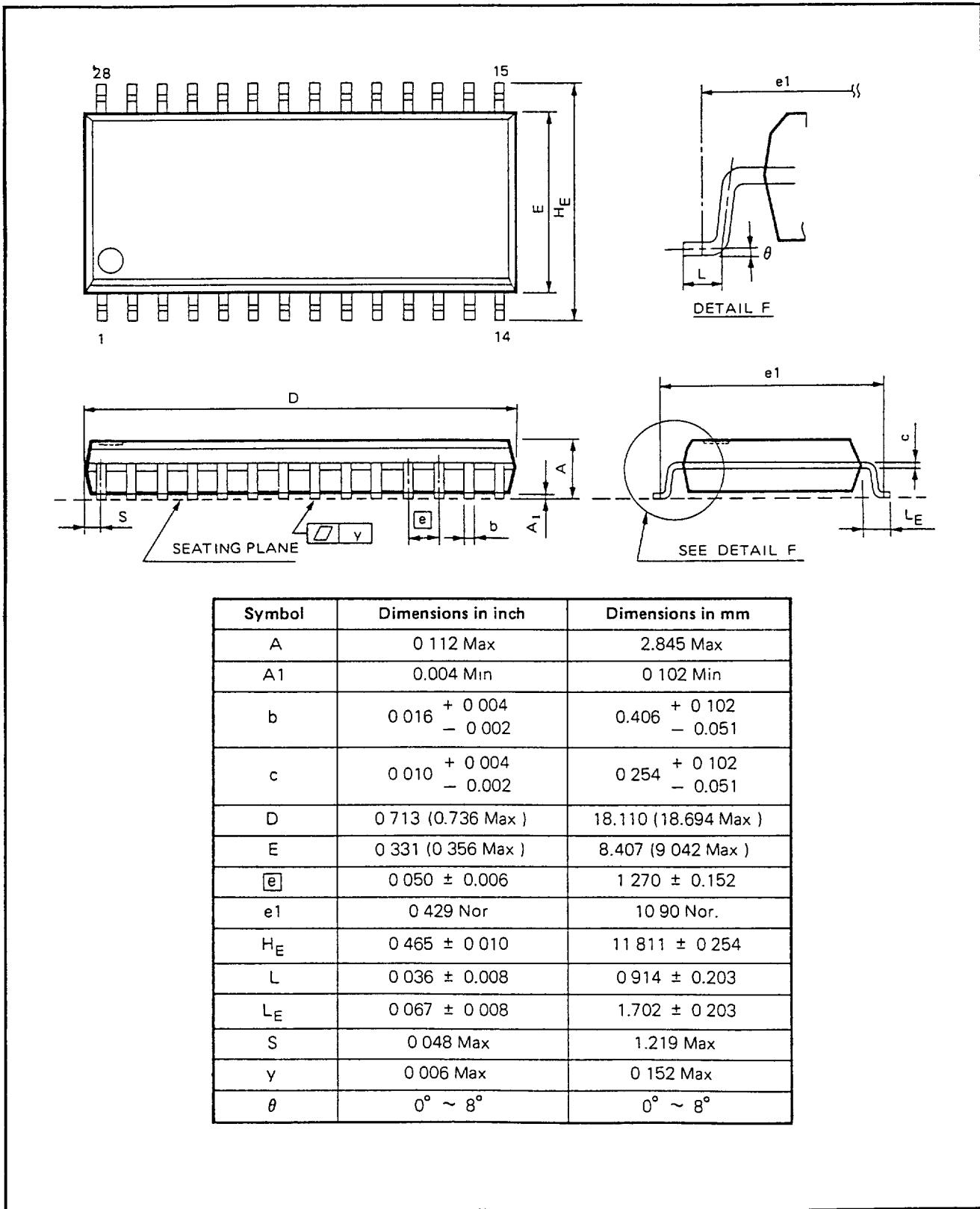
Unit inch/mm



Symbol	Dimensions in inch	Dimensions in mm
A	0.210 Max.	5.334 Max
A1	0.010 Min	0.254 Min.
B	0.018 + 0.004 - 0.002	0.457 + 0.102 - 0.051
B1	0.060 + 0.004 - 0.002	1.524 + 0.102 - 0.051
C	0.010 + 0.004 - 0.002	0.254 + 0.102 - 0.051
D	1.460 (1.470 Max.)	37.084 (37.338 Max.)
E	0.600 ± 0.010	15.240 ± 0.254
E1	0.545 (0.575 Max.)	13.843 (14.605 Max.)
e1	0.100 ± 0.010	2.540 ± 0.254
L	0.130 ± 0.010	3.302 ± 0.254
α	0° ~ 15°	0° ~ 15°
S	0.090 Max.	2.286 Max

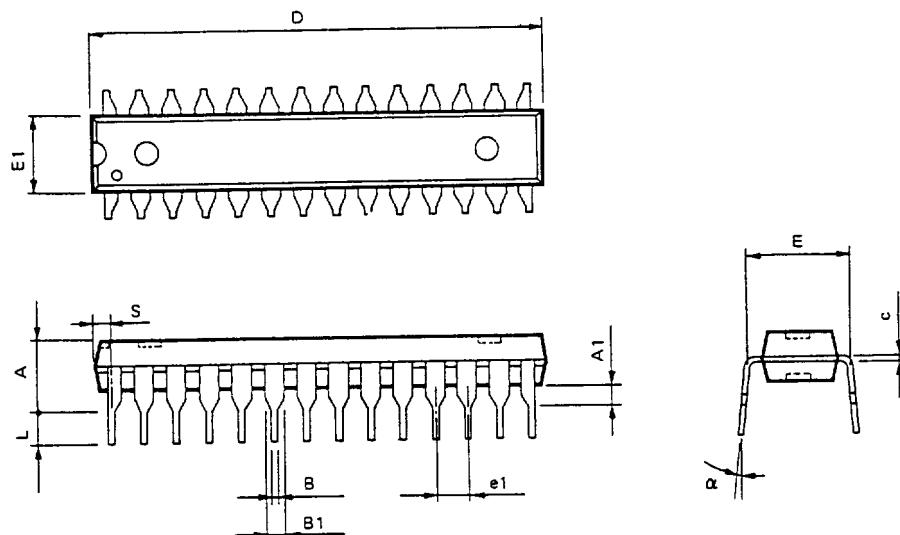
28 Pin Small Outline

Unit inch/mm



28 Pin Skinny Outline

Unit inch/mm

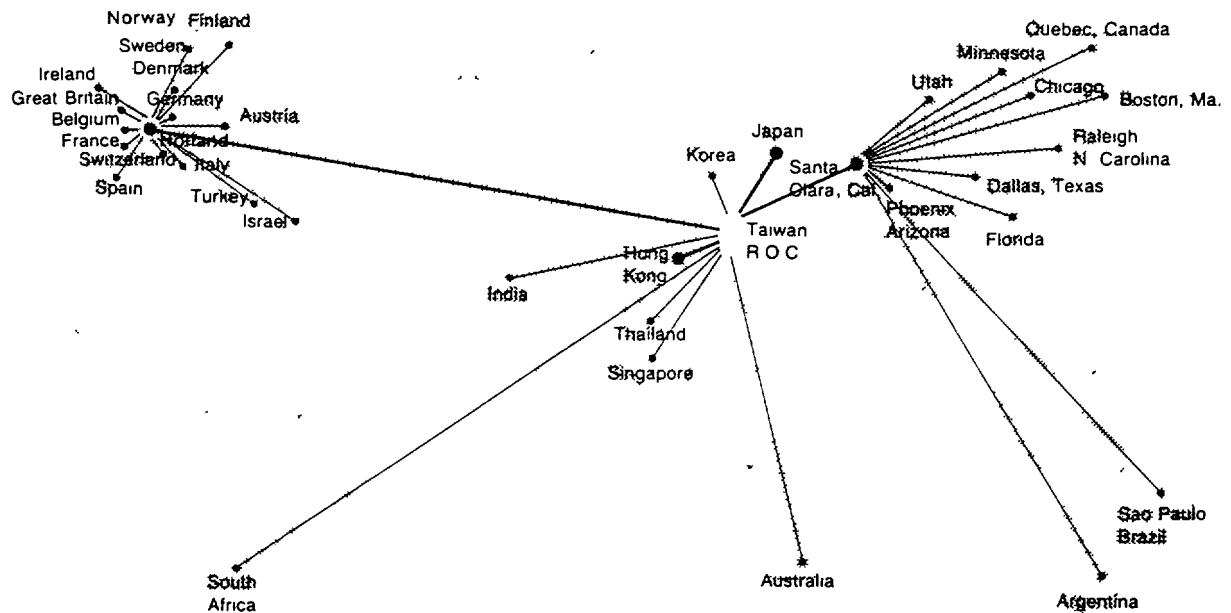


Symbol	Dimensions in inch	Dimensions in mm
A	0 175 Max	4 445 Max.
A1	0 010 Min.	0.254 Min
B	0 018 + 0 004 - 0.002	0.457 + 0 102 - 0.051
B1	0 060 + 0 004 - 0.002	1 524 + 0 102 - 0.051
C	0 010 + 0 004 - 0.002	0.254 + 0 102 - 0.051
D	1 388 (1 400 Max)	35 255 (35 560 Max)
E	0 310 ± 0 010	7 874 ± 0 254
E1	0 288 (0 310 Max)	7 315 (7 874 Max)
e1	0 100 ± 0 010	2 540 ± 0 254
L	0 130 ± 0 010	3 302 ± 0 254
α	0° ~ 15	0° ~ 15°
S	0 055 Max	1 397 Max

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Worldwide Distribution Channels



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